

SOI WAFERS - SPECIFICATION SOI-380-1-10

Rev. 2.2 / 04.04.2003

Bonded Wafer

Diameter :	$100 \pm 0.5\text{mm}$
Thickness :	$391 \pm 10\mu\text{m}$
Primary Flat Orientation :	$\{110\} \pm 1.0^\circ$
Primary Flat Length :	$32.5 \pm 2.5\text{ mm}$
Secondary Flat Location :	No secondary flat
Edge Profile :	Rounded edge
Laser Marking :	On backside of wafers according to PO
Back Surface Quality :	Polished
Front Surface Quality :	No scratches, haze, edge chips, orange peel, defects

Handle Wafer

Doping type	P
Dopant	Boron
Crystal Orientation :	$\{100\}$
Off-Orientation	$0.0 \pm 0.5^\circ$
Resistivity :	1 – 10 Ohmcm
Thickness :	$380 \pm 10\mu\text{m}$

Buried Oxide

Oxide Thickness	$1.00 \pm 0.05\mu\text{m}$
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Device Wafer

Doping type	P
Dopant	Boron
Crystal Orientation :	$\{100\}$
Off-Orientation	$0.0 \pm 0.5^\circ$
Resistivity :	1 – 10 Ohmcm
Thickness :	$10.0 \pm 0.7\mu\text{m}$
Edge non-SOI area :	< 1.2mm (preferably 0mm if not affecting quality)